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PATENT ABSTRACTS OF JAPAN(21) Application number: **10128453**(51) Int'l. Cl.: **C23F 1/12 H01L 21/306**(22) Application date: **12.05.98**(30) Priority: **13.05.97 GB 97 9709659**(71) Applicant: **SURFACE TECHNOL SYST LTD**(43) Date of application publication: **02.12.98**(72) Inventor: **MCQUARRIE ANDREW DUNCAN BOMAN LEE CAMPBELL**(84) Designated contracting states: (74) Representative: **(54) METHOD FOR
ETCHING WORK AND
APPARATUS THEREFOR****(57) Abstract:**

PROBLEM TO BE SOLVED: To improve the efficiency of an etching stage by continuously supplying gaseous XeF₂ and executing etching while the etching is heretofore executed by pulsatively supplying gaseous XeF₂.

SOLUTION: An XeF₂ supplying section 12 consists of an XeF₂ source chamber 16 including a tray and ampoule 17 for an XeF₂ crystal 17a, a tank 18 via a valve 19, a flow rate controller 13 supplied with this material by the tank 18 and a valve 20 between the tank 18 and the flow rate controller 13. Pressure sources 21, 22 are provided respectively to maintain the tank 18 and the XeF₂ source chamber 16 at the sublimation pressure of the XeF₂. This apparatus ensures the stable supply of the XeF₂ to an etching chamber.

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